BC807-16 BC807-25 BC807-40



Mark: 5A. / 5B. / 5C.

PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at currents to 1.0 A. Sourced from Process 78.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		*BC807-16 / -25 / -40	
PD	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
R _{0JA}	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

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$\frac{\text{parameter}}{\text{test Conditions}} \text{Win} \text{Wax} \text{United} \\ \hline \text{Wax} \text{Wax} \text{United} \\ \hline \text{Wax} \text{Wax} \text{Wax} \\ \hline \text{Wax} \text{Wax} \text{Wax} \text{United} \\ \hline \text{Wax} \text{United} \\ \hline \text{Wax} \text{United} \text{Wax} \text{Wax} \text{United} \\ \hline \text{Wax} \text{United} \text{Wax} \text{United} \text{Wax} $	Sumbal			Min	Max	Unite
DFCHARACTERISTICS (any colspan="2">(any colspan="2") (any colspan="	Symbol	Parameter	Test Conditions	IVIIN	wax	Units
$\frac{ a_{BP CCO}}{ a_{BP CCO}} Collector-Emitter Breakdown Voltage I_c = 10 mA, I_b = 0 a_{BP CEO} Collector-Base Breakdown Voltage I_c = 10 µA, I_c = 0 a_{BO} Collector-Base Breakdown Voltage I_c = 10 µA, I_c = 0 a_{BO} Collector-Cutoff Current Voltage I_c = 10 µA, I_c = 0 Collector-Cutoff Current Voltage I_c = 20 V, T_A = 150°C NOCHARACTERISTICS \frac{DC Current Gain I_c = 100 mA, V_{CE} = 1.0 V - 16 100 250 - 250 I_c 400 - 250 I_c 400 0 - 250 I_c 40 0 0 I_c = 500 mA, V_{CE} = 1.0 V - 40 0 0 I_c = 500 mA, V_{CE} = 1.0 V - 40 0 0 I_c = 500 mA, V_{CE} = 1.0 V - 1.2 V - 1.2 V - 1.2 V NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors. Typical Pulsed Current Gain V CR = 1.0 V - 1.2 V - $	OFF CHA	RACTERISTICS				
$\frac{(ae)_{CES}}{(ae)_{CEC}} \frac{Collector-Base Breakdown Voltage}{I_c} = 10 \mu A, I_c = 0$ $\frac{50}{50} \frac{V}{V}$ $\frac{V}{(ae)_{EEO}} \frac{Emitter-Base Breakdown Voltage}{I_c} = 10 \mu A, I_c = 0$ $\frac{50}{50} \frac{V}{V}$ $\frac{V}{aeo} \frac{Collector-Cutoff Current}{V_{CB}} \frac{V}{V_{CB}} = 20 V, T_A = 150^{\circ}C$ $\frac{100}{A} \frac{h}{\mu A}$ $\frac{DN CHARACTERISTICS}{Fe}$ $\frac{DC Current Gain}{I_c = 500 mA, V_{CE}} = 1.0 V \cdot \frac{16}{100} \frac{100}{250} \frac{250}{600}$ $\frac{1}{CE(aat)} \frac{Collector-Emitter Saturation Voltage}{I_c} = 500 mA, V_{CE} = 1.0 V \cdot \frac{16}{100} \frac{100}{250} \frac{250}{600}$ $\frac{1}{CE(aat)} \frac{Collector-Emitter Saturation Voltage}{I_c} = 500 mA, V_{CE} = 1.0 V \cdot \frac{12}{1.2} V$ $NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.$ $Collector-Emitter Saturation Voltage I_c = 500 mA, V_{CE} = 1.0 V \cdot \frac{1.2}{1.2} V$ $NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.$	(BR)CEO	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	45		V
$\frac{ \mathbf{g}_{H} _{EEO}}{ \mathbf{g}_{HO} _{EO}} = \frac{ \mathbf{m}_{H} _{HO} _{EO} = 0 \qquad 5.0 \qquad \forall \qquad \forall \\ \mathbf{g}_{O} _{EO} = 20 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 20 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 mA, \forall_{CE} = 1.0 \lor V \\ \nabla_{CB} = 100 \lor V \\ \nabla_{$	(BR)CES	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	50		V
Collector-Cutoff Current V _{CB} = 20 V V _{CB} = 20 V, T _A = 150°C 100 nA V _{CB} = 20 V, T _A = 150°C 100 nA, A DN CHARACTERISTICS Tre DC Current Gain Ic = 100 mA, V _{CE} = 1.0 V -16 100 250 -25 100 250 -26 400 -25 -40 250 600 -2 -40 250 600 -2 -40 250 600 -2 -40 250 -40 250 -40 250 -40 250 -40 250 -40 -2 -40 250 -40 -2 -2	(BR)EBO	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V
$\frac{P_{E} \\ b C \ Current Gain \\ c \ So mA, V_{CE} \ So mA, V_$	во	Collector-Cutoff Current	V _{CB} = 20 V V _{CB} = 20 V, T _A = 150°C		100 5.0	nA μA
The function of the second se		ACTEDISTICS				
$I_{c} = 100 \text{ mV}, V_{CE} = 1.0 \text{ V} \frac{100}{250} \frac{100}{600} \frac{100}{-20} \frac$			$l_{0} = 100 \text{ mA} \text{ V}_{00} = 1.0 \text{ V}_{0} = 16$	100	250	
$\frac{ c _{CE} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}}{ c _{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}} \frac{40}{40} \frac{600}{0.7} \text{ V}}{ c _{CE(Bat)}}$ Base-Emitter On Voltage $ c _{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}}{1.2 \text{ V}}$ NoTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.	E		- 25	160	400	
$\frac{1}{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V} 40 \text{ 0.7 V} 4$			- 40	250	600	
Typical Pulsed Current Gain $V_{CE} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ Typical Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $V_{CE} = 1.0 \text{ V}$ V_{CE	05 (1)	Collector-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	40		V
Note: All voltages (V) and currents (A) are negative polarity for PNP transistors. Typical Pulsed Current Gain vs Collector Current $u_{d}^{400} \underbrace{\int_{0}^{400} \frac{1}{25 \circ 0} \underbrace{\int_{0}^{1} \frac{1}{125 \circ 0$			10 = 1000000000000000000000000000000000		07	V
vs Collector Current $v_{CE} = 5V$ $v_{CE} = 5V$	NOTE: All volt	Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP	$I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$ $I_{C} = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ transistors.		0.7	
	Typica	Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 500 \text{ mA}, V_{CE} = 1.0 \text{ V}$ transistors. Collector-E	Emitter S	0.7 1.2	∨ ∨
$\mathbf{y}_{u} = \mathbf{y}_{u} $	Typica	ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current	$\frac{1_{C} = 500 \text{ mA}, _{B} = 50 \text{ mA}}{1_{C} = 500 \text{ mA}, _{CE} = 1.0 \text{ V}}$ transistors. Collector-E $\sum_{\underline{w}} \text{ Voltage vs}$	Emitter S Collecto	aturation	n t
$H_{u} = 0.1$	Typica	al Characteristics Typical Pulsed Current Gain vs Collector Current	Collector = Coll	Emitter S Collecto	aturation	• • • •
$\begin{array}{c} \mathbf{G}_{2} \\ \mathbf{G}_{1} \\ \mathbf{G}_{1$	Typica	ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current	Collector-E $Collector-E$ $Voltage v s$	Emitter S Collecto	aturation	v v v v
$ \begin{array}{c} $		ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current	$Collector = 1.0 V$ $Collector = 1.0 V$ $Collector = 1.0 V$ $Collector = 0.6 - \beta = 10$	Emitter S Collecto	aturation	v ∨ ∨ v
$ \begin{array}{c} $		al Characteristics Typical Pulsed Current Gain vs Collector Current VcE = 5V VcE = 5V VcE = 5V	Collector = 1.0 V $Collector = 1.0 V$ $Collector = 0.6 P = 10 P$ $Collector = 0.6 P = 10 P$	Emitter S Collecto	aturation	v ∨ ∨ v
$ \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \end{array}\\ \end{array}\\ \end{array} \\ \begin{array}{c} \end{array}\\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \begin{array}{c} \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \end{array} \\ \begin{array}{c} \end{array} \\ \end{array} \\$		ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current V _{CE} = 5V	$Collector-E$ $Collector-E$ $Voltage v s$ $H_{0,3}$ $H_{0,3}$	Emitter S Collecto	aturation	v ∨ ∨ v
$ \begin{array}{c c} & & & & \\ & & & & \\ & & & & \\ & & & &$		ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current U	$ \begin{array}{c} C_{C} = 500 \text{ mA}, $	Emitter S Collecto	aturation r Current	-40 °C
$I_{c} - COLLECTOR CURRENT (A) = I_{c} - COLLECTOR CURRENT (A$		ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current V _{CE} = 5V V _{CE} = 5V -40 °C	$\begin{array}{c} Collector = 1.0 \text{ V} \\ \hline C = 500 \text{ mA}, \text{ V}_{CE} = 1.0 $	Emitter S Collecto	aturation r Current	v ∨ ∨ v
I_c - COLLECTOR CURRENT (A) > I_c - COLLECTOR CURRENT (A)		ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current VcE = 5V -40 °C	$ \begin{array}{c} Collector-E \\ $	Emitter S Collecto	aturation r Current	V V V
		Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5V$ $V_{CE} = 5V$ $V_{CE} = 5V$ $V_{CE} = 5V$ $V_{CE} = 100000000000000000000000000000000000$	$ \begin{array}{c} $	Emitter S Collecto	aturation	v V V t 25 °C 1 1.5
		Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5V$ $V_{CE} = 5V$ V	$ \begin{array}{c} $	Emitter S Collector	aturation r Current	v V V t 25 °C 1 1.5
		Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5V$ $V_{CE} = 5V$ V	$ \begin{array}{c} $	Emitter S Collecto	aturation r Current	v V V
		Base-Emitter On Voltage ages (V) and currents (A) are negative polarity for PNP- al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5V$ $V_{CE} = 1000$ $V_{CE} = 10000$ $V_{CE} = 1000$ $V_{CE} = 10000$ $V_{CE} = 10000$ $V_{CE} = 10000$ $V_{CE} = 10000$ $V_{CE} = 10000$ $V_{CE} = 100000$ $V_{CE} = 100000$ $V_{CE} = 10000000$ $V_{CE} = 100000000000000000000000000000000000$	$ \begin{array}{c} $	Emitter S Collector	aturation r Current	v V V

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